

Abstract of the Disclosure

A high voltage semiconductor device, including: a high concentration collector area of a first conductive type; a low concentration collector area of a first conductive type formed on the high concentration collector area; a base area of a second conductive type formed on the low concentration collector area and having a trench perforating the low concentration collector area in a vertical direction at the edge of the trench; a high concentration emitter area of a first conductive type formed on a predetermined upper surface of the base area; and an emitter electrode, a base electrode, and a collector electrode isolated from one another and connected to the emitter area, the base area, and the collector area, respectively. High breakdown voltage can be obtained with a narrow junction termination area due to the trench.